

MAGNETORESISTIVE DEVICE AND METHOD FOR FORMING THE SAME

ABSTRACT

5 According to embodiments of the present invention, a magnetoresistive device is provided. The magnetoresistive device includes a free magnetic layer structure having a variable magnetization orientation, and a synthetic antiferromagnetic layer structure including at least three ferromagnetic layers arranged one over the other and antiferromagnetically coupled, each ferromagnetic layer having a fixed magnetization
10 orientation, wherein the free magnetic layer structure and the synthetic antiferromagnetic layer structure are arranged one over the other. According to further embodiments of the present invention, a method for forming a magnetoresistive device is also provided.

Figure 3